

# DTC125TUA / DTC125TKA / DTC125TSA

Transistors

## Digital transistor (built-in resistor)

### DTC125TUA / DTC125TKA / DTC125TSA

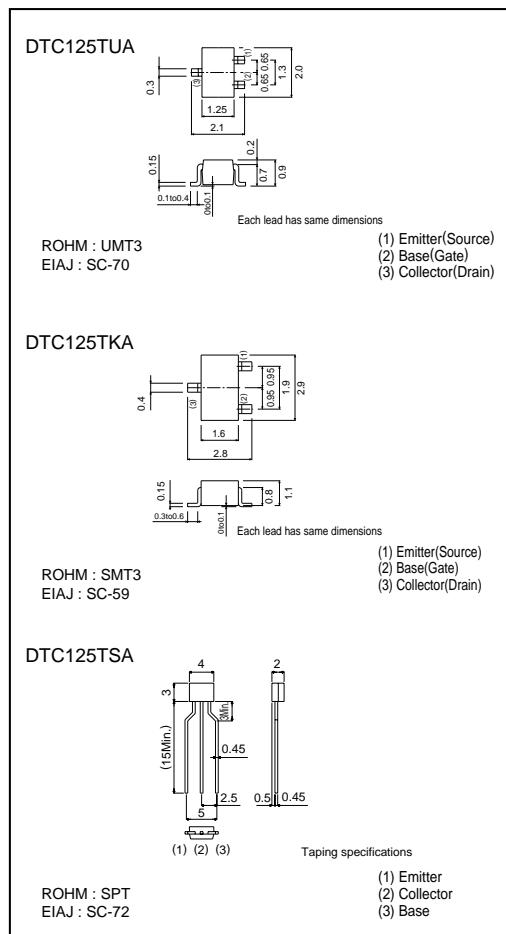
#### ●Features

- 1) Built-in bias resistors enable the configuration of an inverter circuit without connecting external input resistors.
- 2) The bias resistors consist of thin-film resistors with complete isolation to allow negative biasing of the input, and parasitic effects are almost completely eliminated.
- 3) Only the on / off conditions need to be set for operation, making device design easy.
- 4) Higher mounting densities can be achieved.

#### ●Absolute maximum ratings ( $T_a = 25^\circ\text{C}$ )

Parameter	Symbol	Limits	Unit
Collector-base voltage	$V_{CBO}$	50	V
Collector-emitter voltage	$V_{CEO}$	50	V
Emitter-base voltage	$V_{EBO}$	5	V
Collector current	$I_C$	100	mA
Collector power dissipation	$P_C$	200	mW
DTC125TUA / DTC125TKA		300	
DTC125TSA			
Junction temperature	$T_J$	150	°C
Storage temperature	$T_{STG}$	-55 ~ +150	°C

#### ●External dimensions (Units : mm)



#### ●Package, marking, and packaging specifications

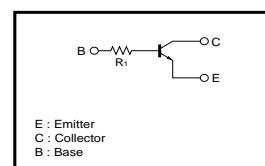
Part No.	DTC125TUA	DTC125TKA	DTC125TSA
Package	UMT3	SMT3	SPT
Marking	0A	0A	—
Packaging code	T106	T146	TP
Basic ordering unit (pieces)	3000	3000	5000

#### ●Electrical characteristics ( $T_a = 25^\circ\text{C}$ )

Parameter	Symbol	Min.	Typ.	Max.	Unit	Conditions
Collector-base breakdown voltage	$BV_{CBO}$	50	—	—	V	$I_C = 50\mu\text{A}$
Collector-emitter breakdown voltage	$BV_{CEO}$	50	—	—	V	$I_C = 1\text{mA}$
Emitter-base breakdown voltage	$BV_{EBO}$	5	—	—	V	$I_E = 50\mu\text{A}$
Collector cutoff current	$I_{CBO}$	—	—	0.5	$\mu\text{A}$	$V_{CB} = 50\text{V}$
Emitter cutoff current	$I_{EBO}$	—	—	0.5	$\mu\text{A}$	$V_{EB} = 4\text{V}$
Collector-emitter saturation voltage	$V_{CE(\text{sat})}$	—	—	0.3	V	$I_C = 0.5\text{mA}, I_B = 0.05\text{mA}$
DC current transfer ratio	$h_{FE}$	100	250	600	—	$I_C = 1\text{mA}, V_{CE} = 5\text{V}$
Input resistance	$R_I$	140	200	260	$\text{k}\Omega$	—
Transition frequency	$f_T$	—	250	—	MHz	$V_{CE} = 10\text{V}, I_E = -5\text{mA}, f = 100\text{MHz}$ *

\* Transition frequency of the device.

#### ●Circuit schematic



**ROHM**